

From Research to
Production



RIBER
60 YEARS OF
PERFORMANCE

EMERGING GROWTH OPPORTUNITIES FOR MBE IN GAN

RIBER

Brian Miller, Business Development



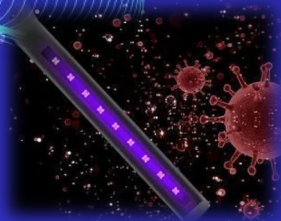
Brussels, April 17th

III-N Applications & Market

Power & RF applications



Optoelectronic applications / UVC-hygiene, AR/VR, wearables, displays



RIBER addresses the **unique features required for MBE of GaN** through a **nitride specific product range** of MBE systems and components. **Customer's data in some emerging markets that could feature MBE** are shown and we look ahead **towards new concepts**.

RIBER : a brief history

RIBER
60 YEARS OF
PERFORMANCE



Molecular Beam Epitaxy solutions
More than 920 Riber/VG MBE
SYSTEMS

MBE Cells
More than 12000 effusion sources



MBE experts



Paris, France



Since 1964



1978 : 1st commercial
MBE system

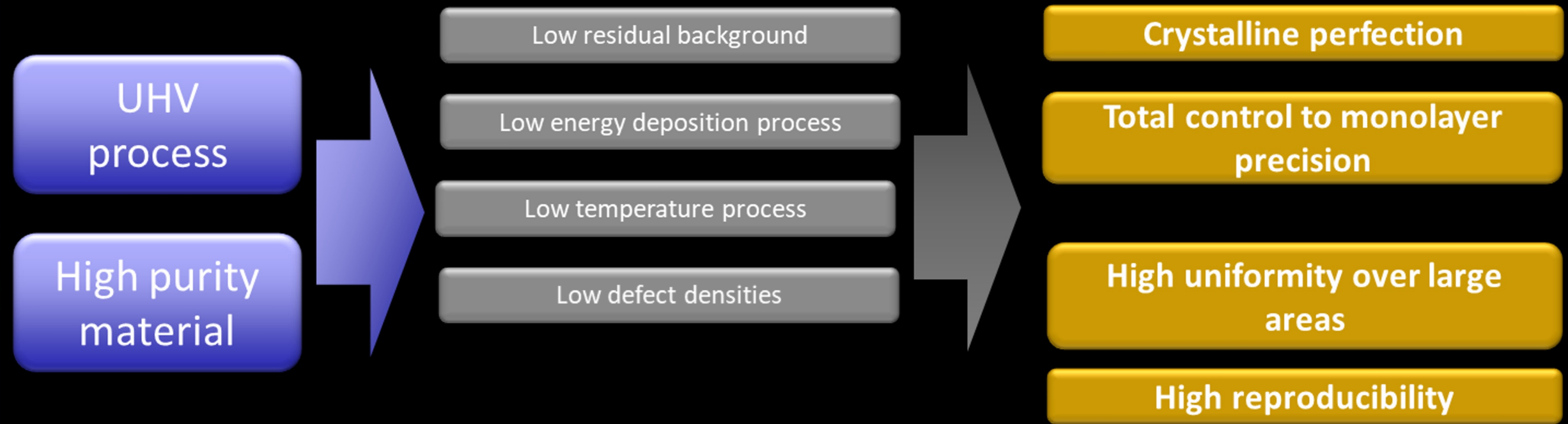


120 employees



ISO 9001

Riber and Nitrides – Why MBE ?



low growth temperature:

→ Impact on epilayer quality & device performance

**Highly doped n-type
GaN:Si possible**

**High Al content readily
achieved**

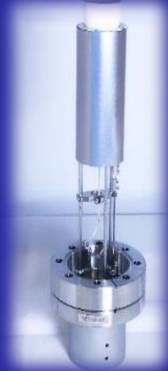
**Precise Tunnel
Junction doping**

Riber and Nitrides – the story so far

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Ammonia injector



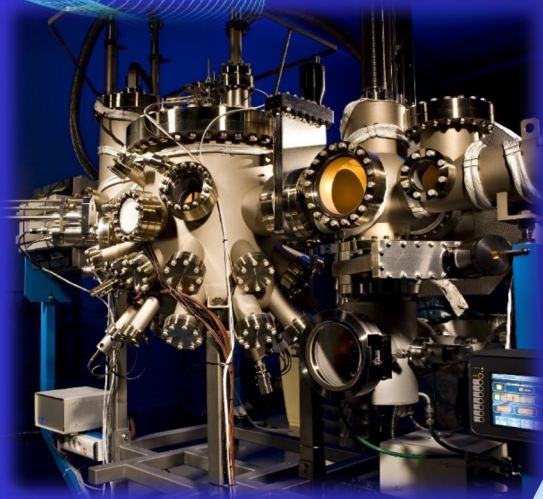
Aluminum effusion cell



Nitrogen RF plasma cell



Magnesium valved cracker cell- VCOR



1997
First Ammonia-
GaN dedicated
system

Aluminum
dedicated
effusion cell

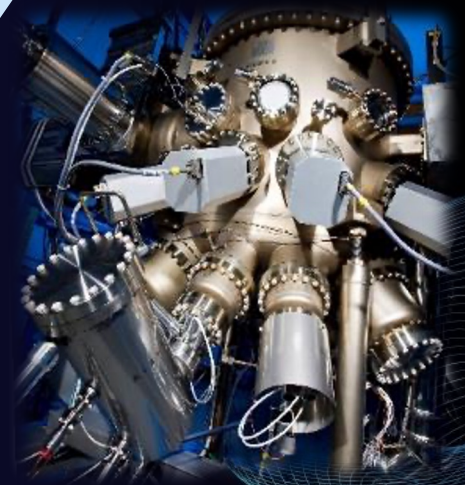
RF plasma
source

Mg Valved
source

Multi 4" NH₃
production
system

High capacity
effusion cell

2020
Multi 4" / Single 8"
NH₃ + PAMBE
production system



4x4" MBE 49



Nitride specific MBE reactors – R&D to Production

Fully automated GaN system RIBER MBE 49



0.2 to 2000 sccm NH_3
injection

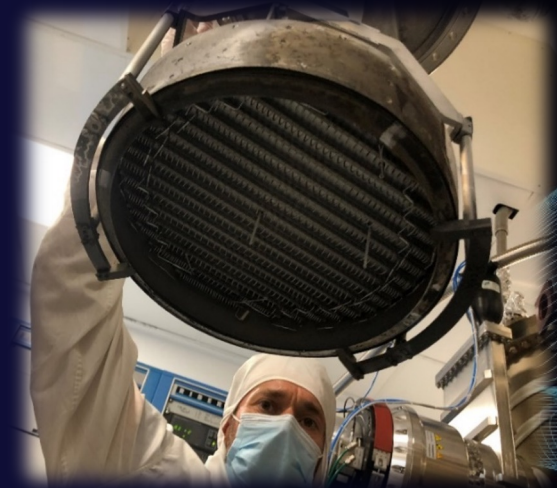
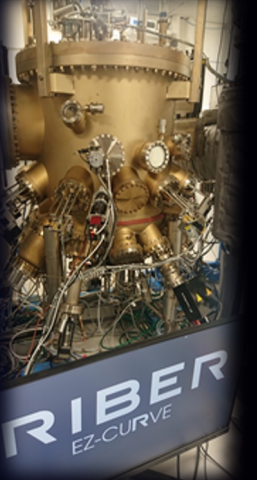
Automated NH_3
regeneration

15 platen capacity / 1x 200
mm / 3x 100 mm / 5x 75 mm

10 cell ports : Ga, Al, In, Si,
Mg, N^* , NH_3

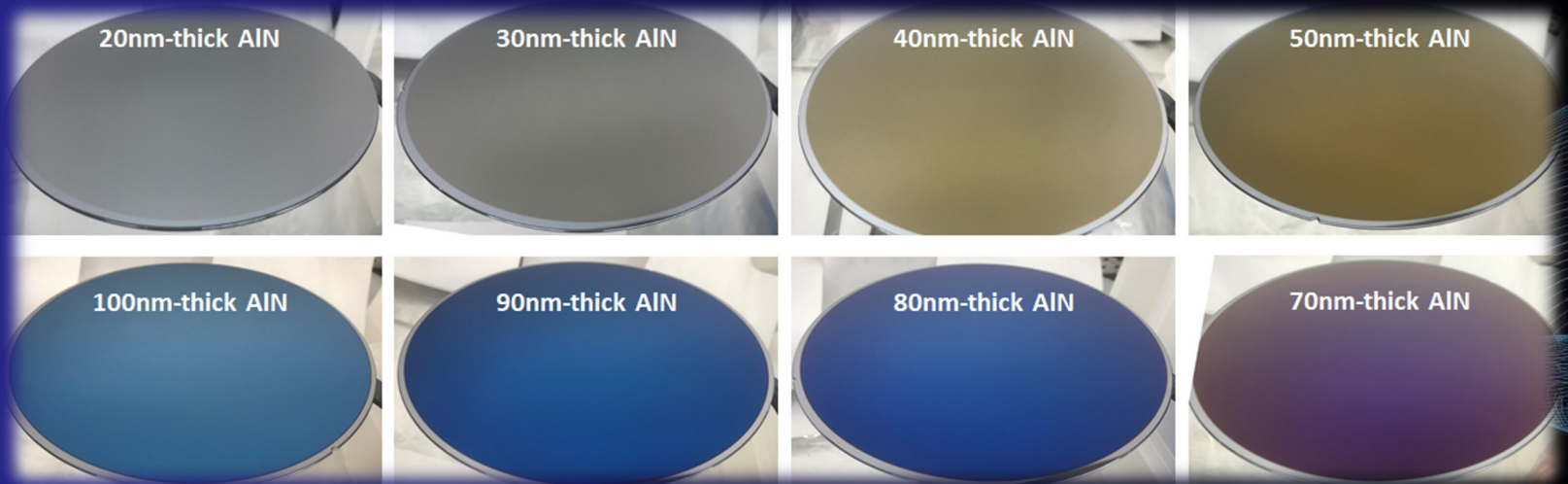
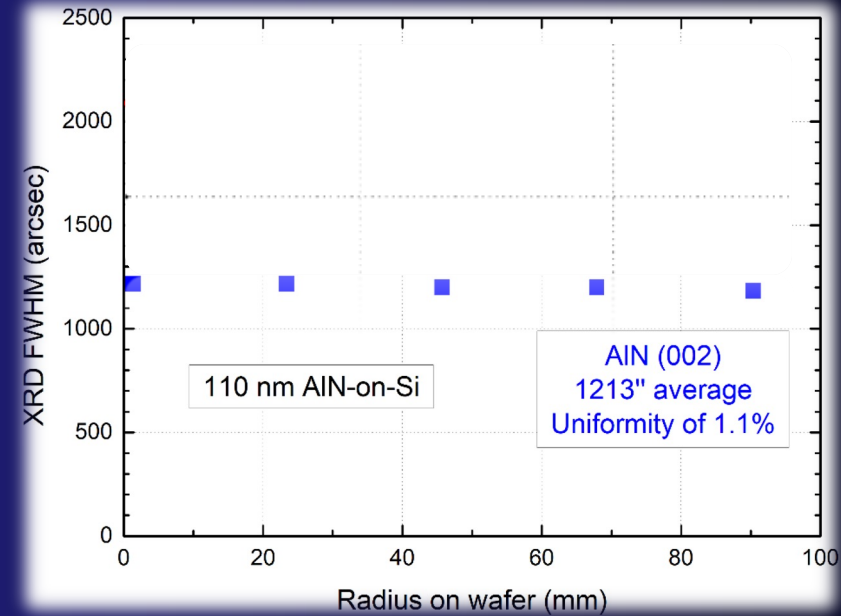
RHEED, wafer curvature
(RIBER EZ-Curve)

**Process transfer to
200 mm (Si)**

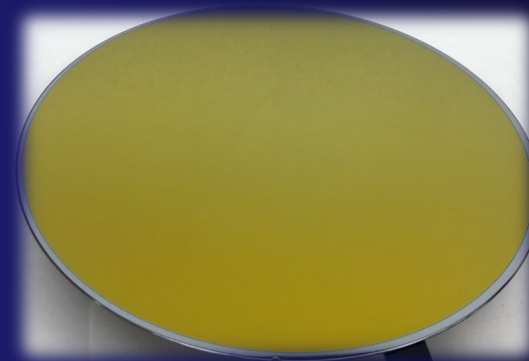
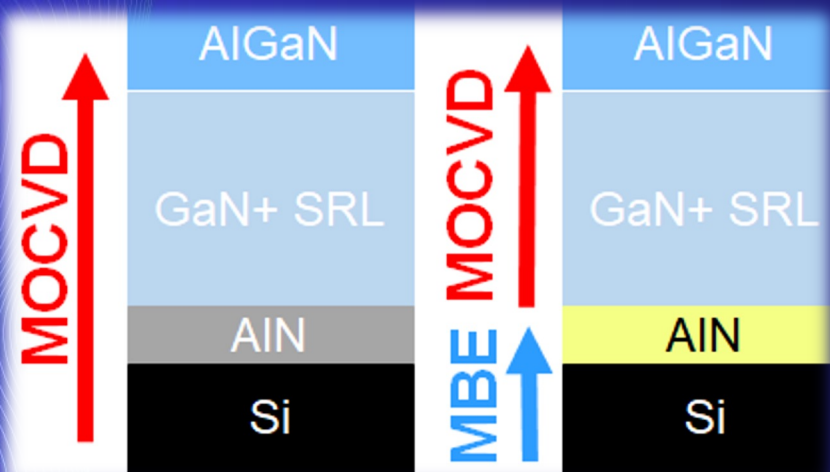


Emerging markets – AlN-on-Si 200 mm templates

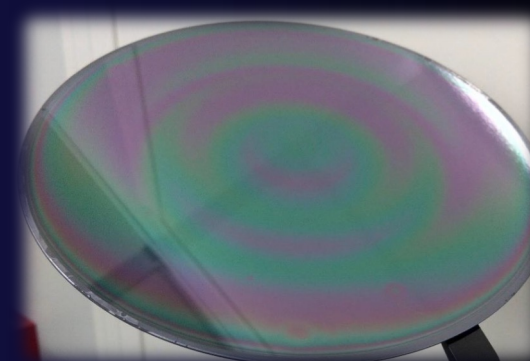
- Temperature uniformity: 3 °C
- **No slip lines**
- State-of-the-art crystal quality
- Real-time curvature monitoring (RIBER EZ-Curve)
- **High reproducibility**



Emerging markets – AlN-on-Si 200 mm templates

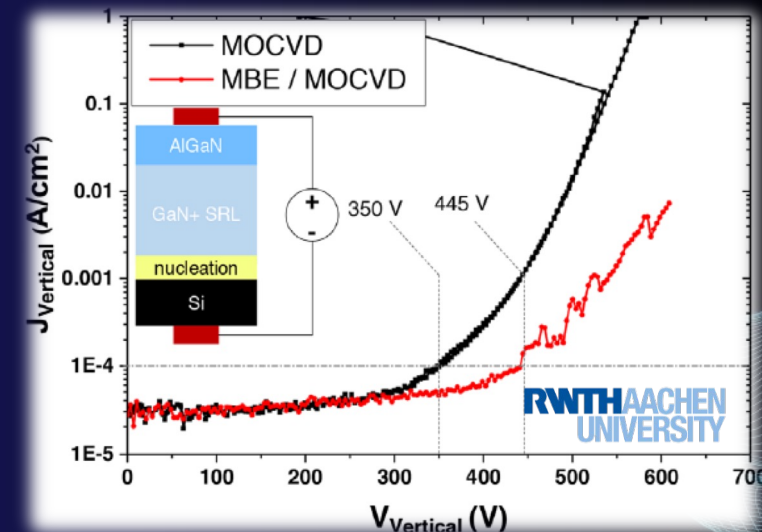


AlN-on-Si 8" Template



Hybrid GaN-on-Si 8"

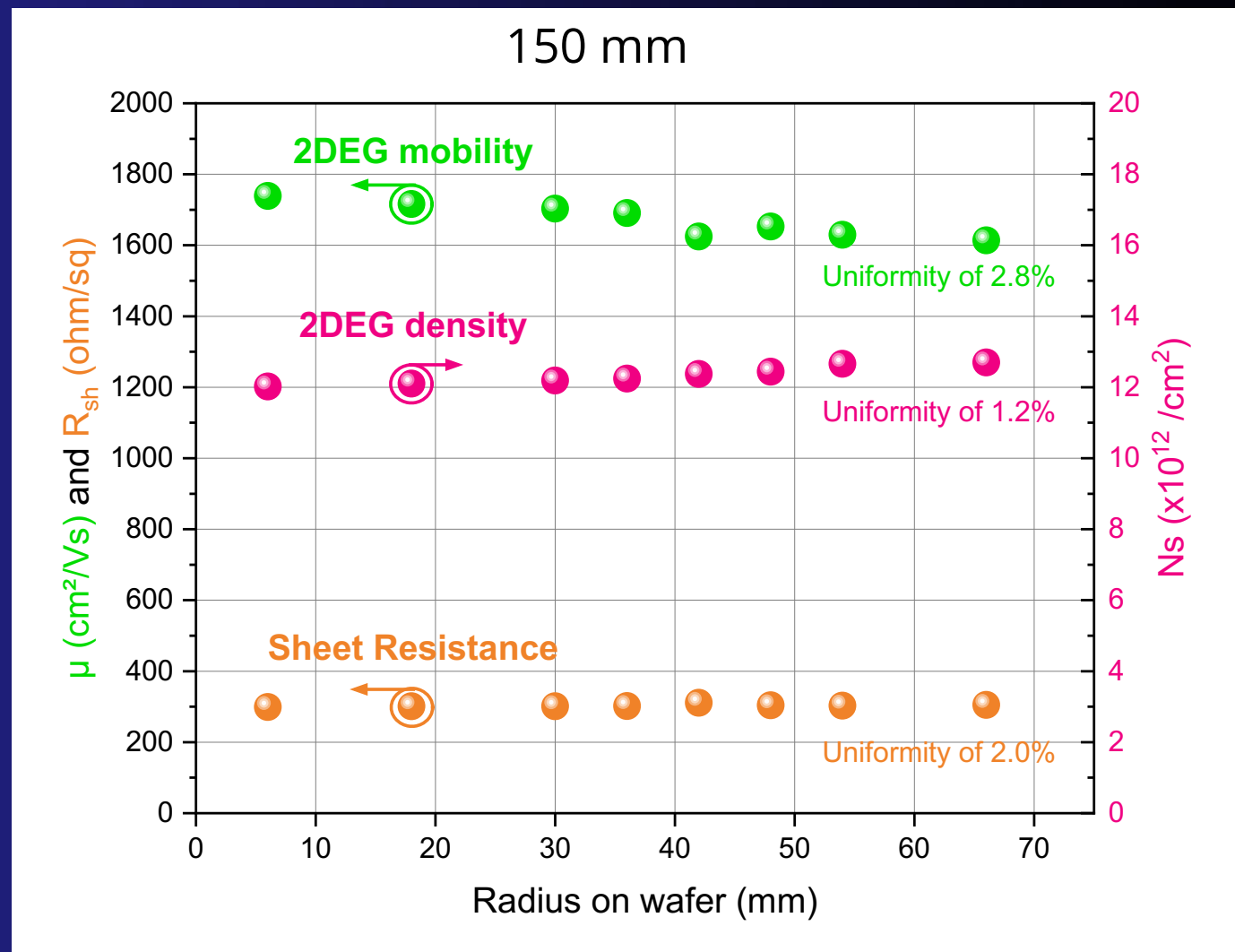
- **MOCVD re-growth validated** (Aixtron and Veeco) – no impact from MBE template air exposure or substrate holder exclusion zone
- **Reduced Substrate Bow** due to thin AlN MBE template layers
- **Gain in device blocking capability** - Sharp, clean AlN/Si interface, suppresses parasitics



Beyond templates – MBE HEMT

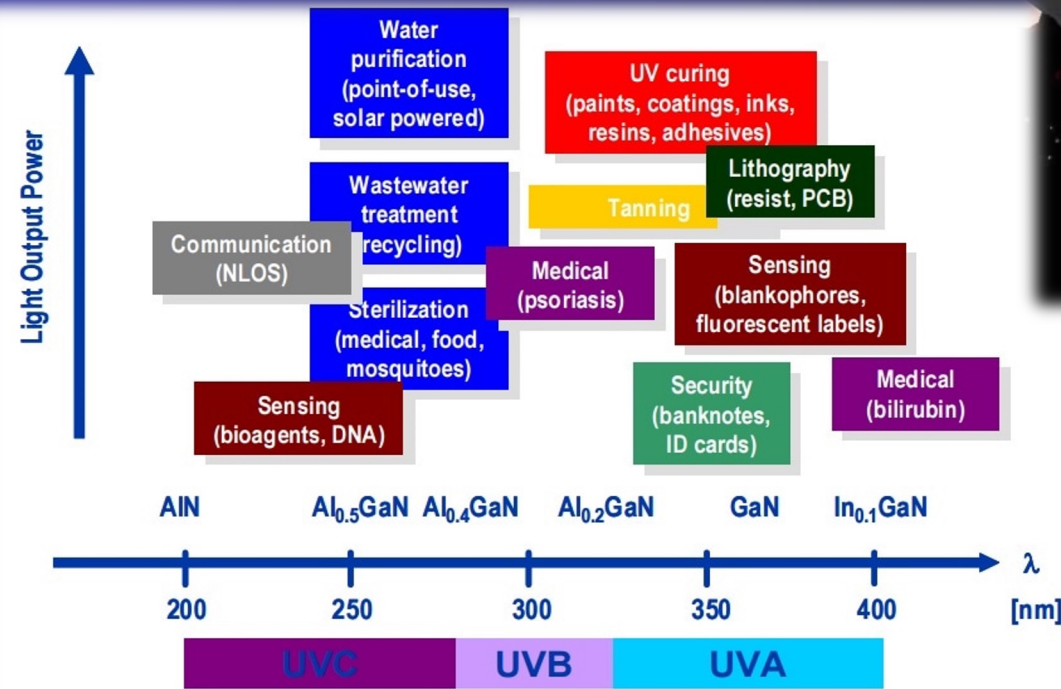
RF applications

Simplified structure
< 800 nm total thickness

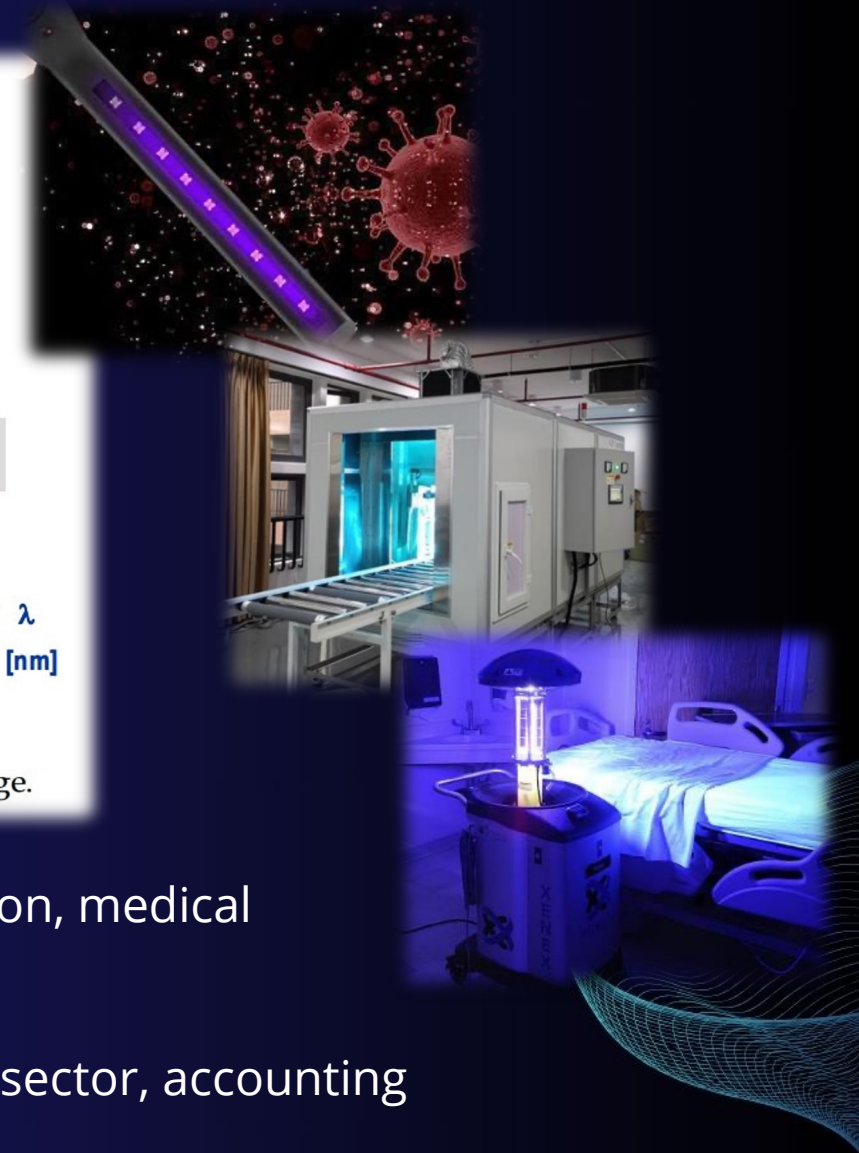


Excellent 2 DEG uniformity

UVC Light Source Market set for Rapid Growth



Applications for LEDs in the UVA, UVB, and UVC wavelength range.



- Deep ultraviolet light is widely used in air sterilization, surface sanitation, medical equipment, water purification, industrial curing and other fields
- According to market segmentation analysis, sterilization is the largest sector, accounting for 54% of the total.

Typical UVC LED Structure Grown by MBE

Sophisticated structure **with high Al content**

p- GaN (a)
p-Al _{0.45} Ga _{0.55} N
p-Al _{0.85} Ga _{0.15} N
Al _{0.8} Ga _{0.2} N
Al _{0.65} Ga _{0.35} N
Al _{0.8} Ga _{0.2} N
n-Al _{0.55} Ga _{0.45} N
n-Al _{0.85} Ga _{0.15} N
n-Al _{0.55} Ga _{0.45} N
n-Al _{0.6} Ga _{0.4} N
HT - AlN
Sapphire (0001)

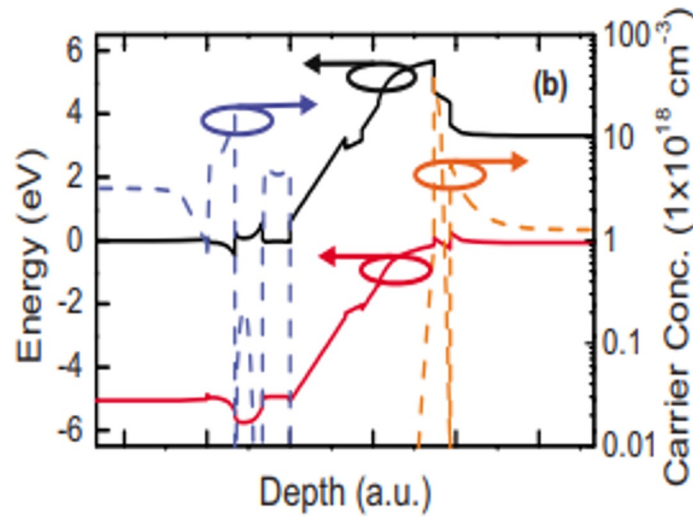
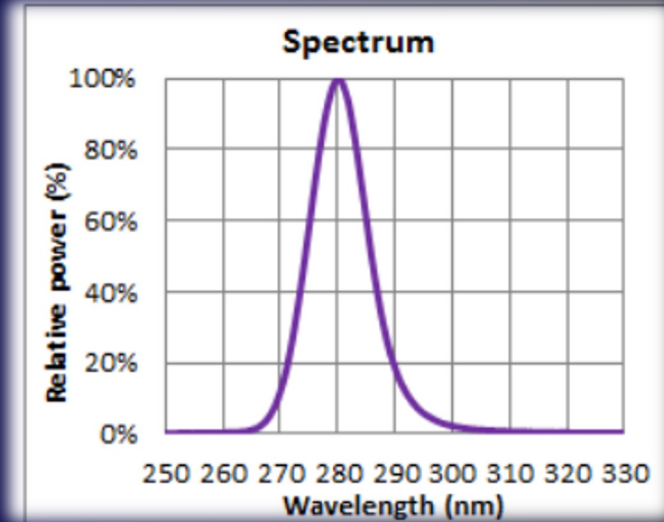
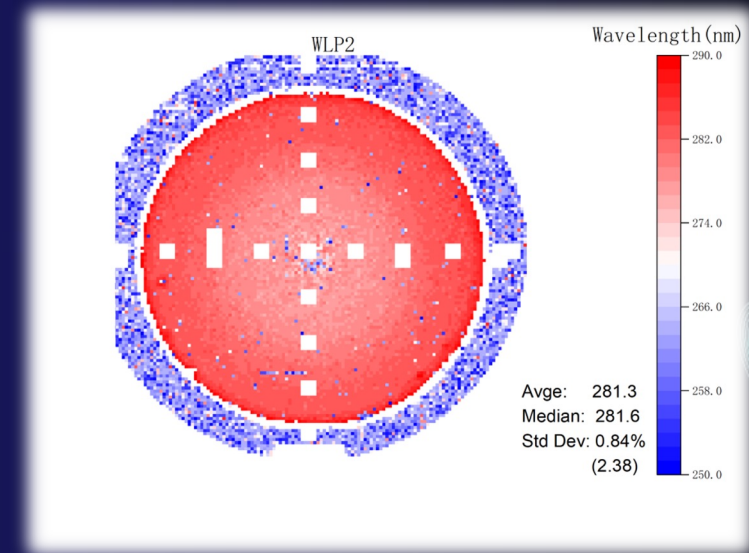


FIG. 3. (Color online) (a) Schematic of the investigated deep UV LED structure; (b) thermal equilibrium band diagram and carrier densities of the structure shown in Fig. 3(a).

<https://doi.org/10.1063/1.3559842>



Spectral
selectivity

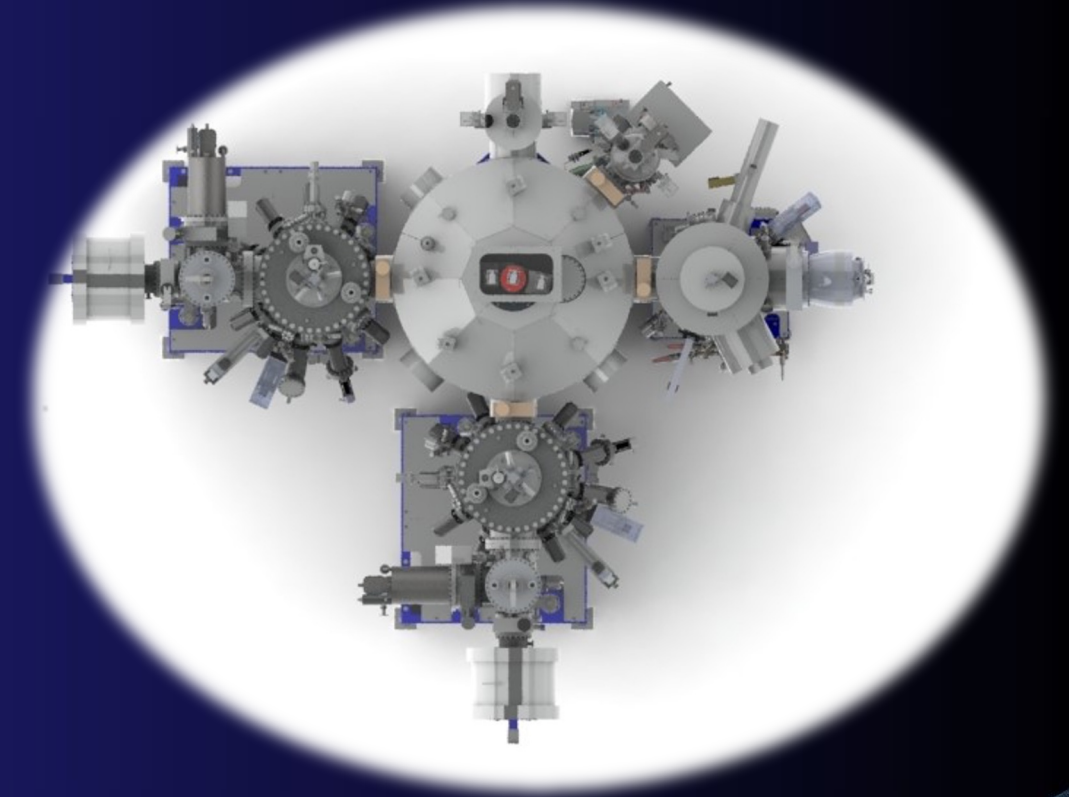
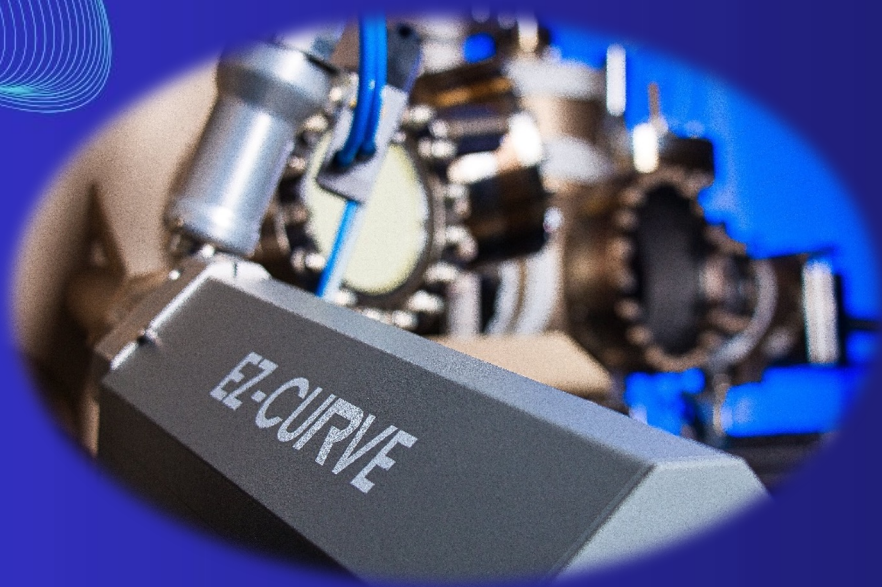


Uniformity Data

Looking Ahead – Continued Innovation

New in - situ monitoring instrumentation

Substrate bow measurement & monitoring of relaxation thickness limits

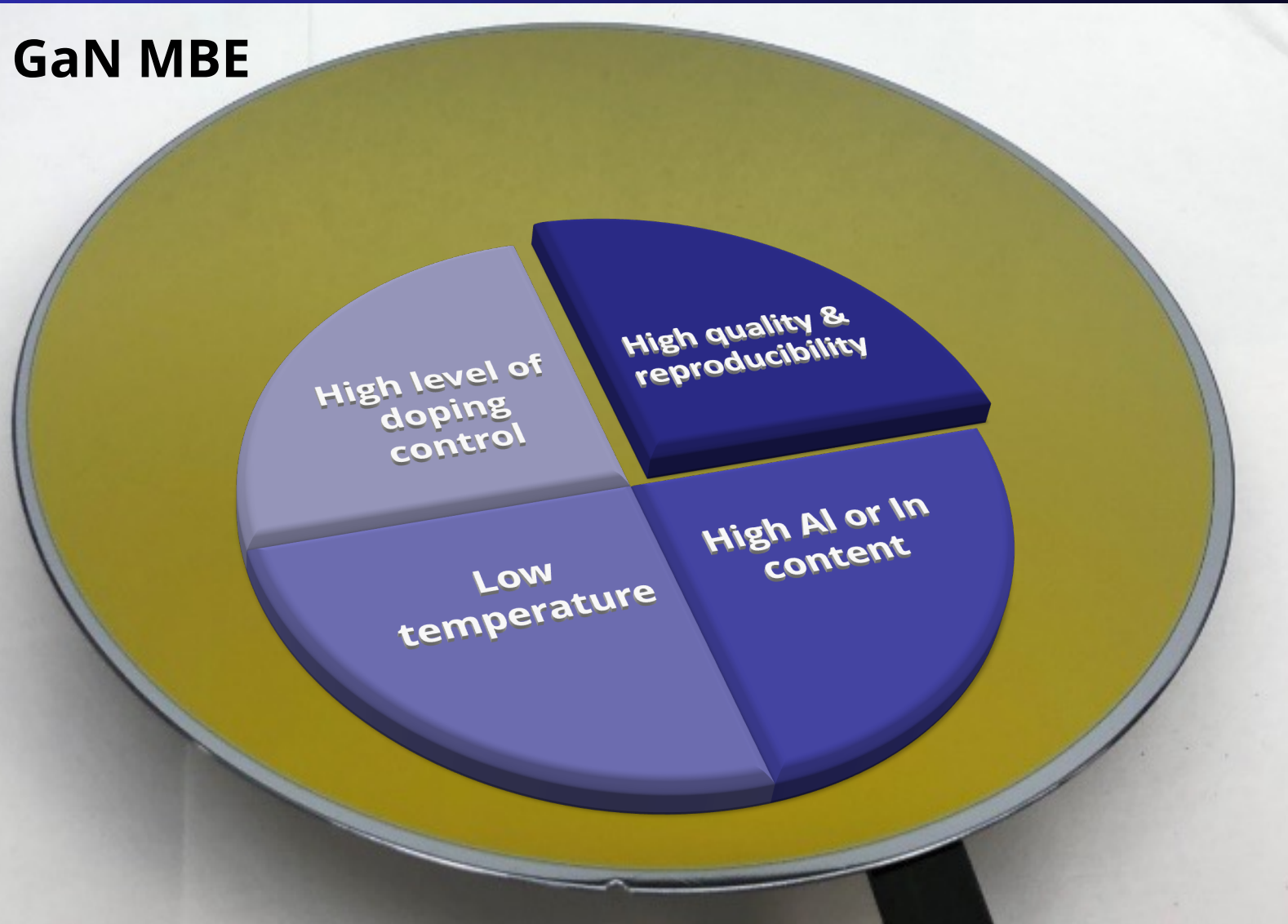


From multi wafer to single wafer:
Compact 6" (8") single wafer reactors +
cluster

*Optimization of pressure during growth and
pumping speed "by design"*

Concluding remarks

GaN MBE



Data Server



Wireless Charging



Acknowledgements & special thanks to:

Dr. Yitao Liao - CEO, Liyu Semiconductor Co. Ltd.

Fabrice Semond, Stephanie Renesson, André Bonnardot – EasyGaN

Claudine Payen, Samuel Matta, Ohann Choolakian, Romain Bruder - RIBER

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INNOVATIVE SOLUTION FOR SEMICONDUCTOR INDUSTRY

MBE IS OUR DNA



RIBER